

MITSUBISHI IGBT MODULES
CM100DY-24H
 HIGH POWER SWITCHING USE
 INSULATED TYPE

CM100DY-24H



- IC 100A
- VCES 1200V
- Insulated Type
- 2-elements in a pack
- UL Recognized

Yellow Card No. E80276
 File No. E80271

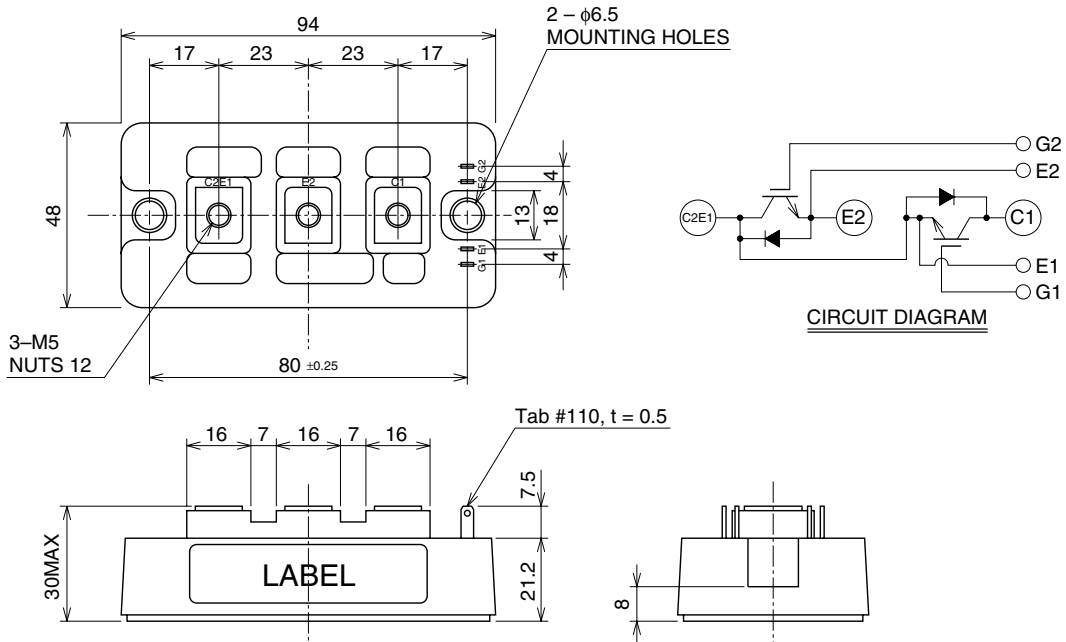
APPLICATION

UPS, NC machine, AC-Drive control, Servo, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm

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ABSOLUTE MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	1200	V
V _{GES}	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	T _C = 25°C	100	A
I _{CM}		Pulse (Note 2)	200	
I _E (Note 1)	Emitter current	T _C = 25°C	100	A
I _{EM} (Note 1)		Pulse (Note 2)	200	
P _C (Note 3)	Maximum collector dissipation	T _C = 25°C	780	W
T _J	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +125	°C
V _{iso}	Isolation voltage	Main terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main terminal M5	1.47 ~ 1.96	N • m
		Mounting holes M6	1.96 ~ 2.94	N • m
—	Weight	Typical value	270	g

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	—	—	1	mA
V _{GE(th)}	Gate-emitter threshold voltage	I _C = 10mA, V _{CE} = 10V	4.5	6	7.5	V
I _{GES}	Gate leakage current	±V _{GE} = V _{GES} , V _{CE} = 0V	—	—	0.5	µA
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 100A, V _{GE} = 15V (Note 4)	—	2.5	3.4	V
C _{iss}	Input capacitance	V _{CE} = 10V, V _{GE} = 0V	—	—	7	nF
C _{oss}	Output capacitance	V _{CE} = 10V, V _{GE} = 0V	—	—	4	nF
C _{res}	Reverse transfer capacitance		—	—	—	—
Q _G	Total gate charge	V _{CC} = 600V, I _C = 100A, V _{GE} = 15V	—	500	—	nC
t _{d(on)}	Turn-on delay time	V _{CC} = 600V, I _C = 100A	—	—	250	ns
t _r	Turn-on rise time	V _{GE1} = V _{GE2} = 15V	—	—	350	
t _{d(off)}	Turn-off delay time	RG = 3.1Ω, Inductive load switching operation	—	—	300	
t _f	Turn-off fall time		—	—	350	
V _{EC} (Note 1)	Emitter-collector voltage	I _E = 100A, V _{GE} = 0V	—	—	3.5	V
t _{rr} (Note 1)	Reverse recovery time	I _E = 100A	—	—	250	ns
Q _{rr} (Note 1)	Reverse recovery charge	die/dt = -200A/µs	—	0.74	—	µC
R _{th(j-c)Q}	Thermal resistance	IGBT part (1/2 module)	—	—	0.16	°C/W
R _{th(j-c)R}		FWDi part (1/2 module)	—	—	0.35	
R _{th(c-f)}	Contact thermal resistance	Case to fin, Thermal compound Applied (1/2 module)	—	—	0.13	

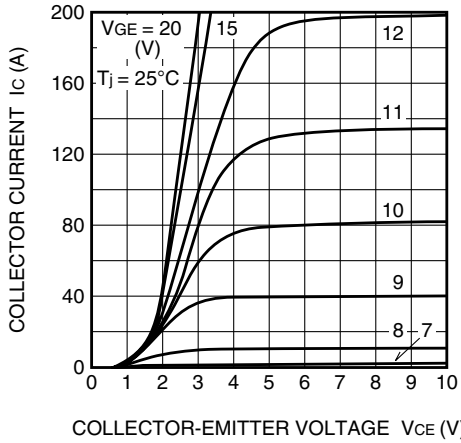
- Note 1. I_E, I_{EM}, V_{EC}, t_{rr}, Q_{rr} & die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).
 2. Pulse width and repetition rate should be such that the device junction temperature (T_J) does not exceed T_{Jmax} rating.
 3. Junction temperature (T_J) should not increase beyond 150°C.
 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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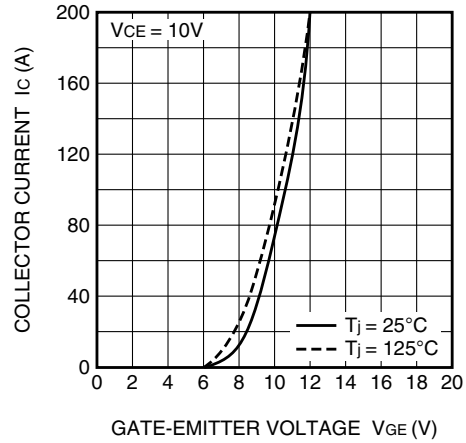
HIGH POWER SWITCHING USE
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PERFORMANCE CURVES

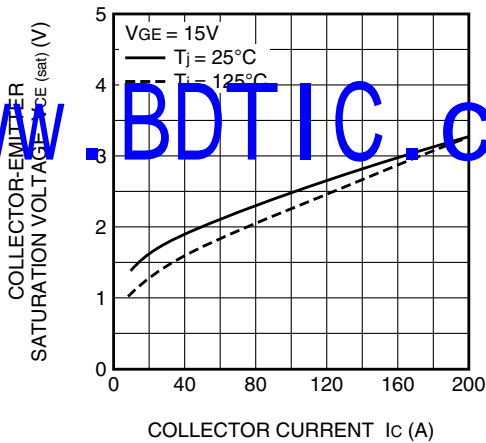
OUTPUT CHARACTERISTICS (TYPICAL)



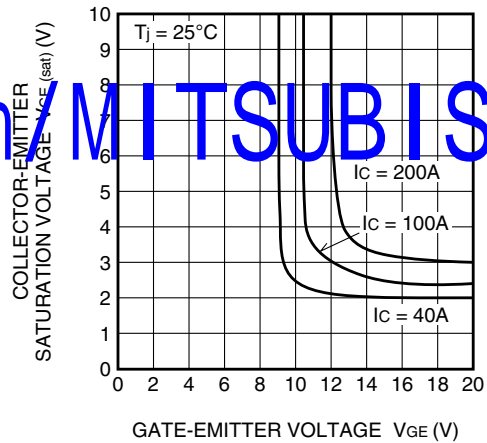
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

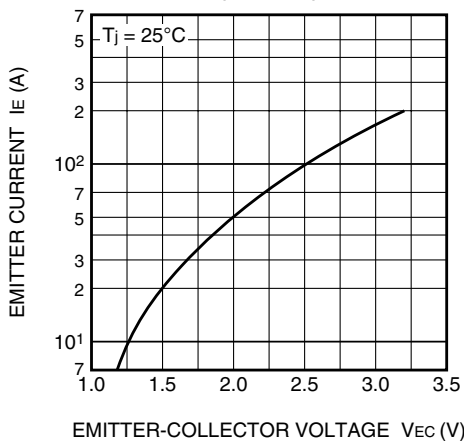


COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

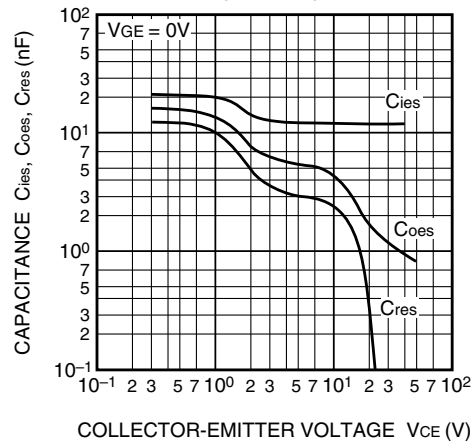


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FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



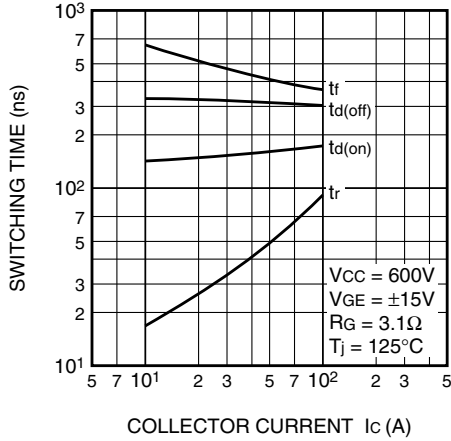
CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)



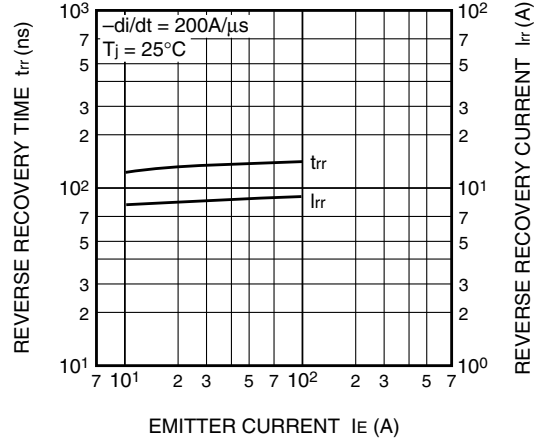
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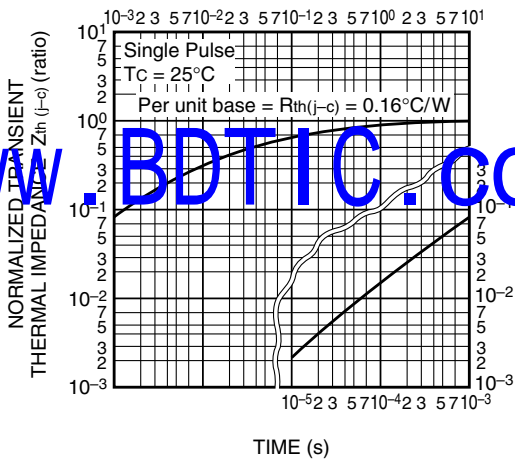
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



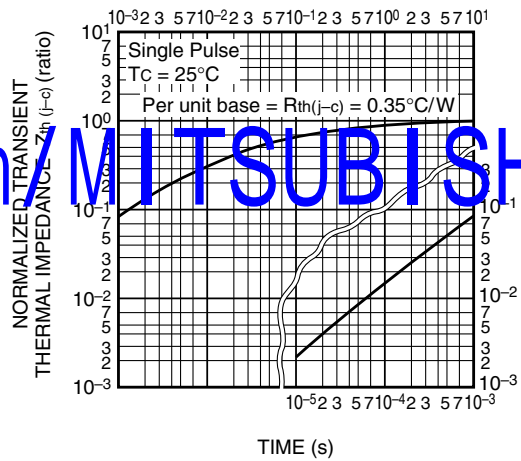
REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



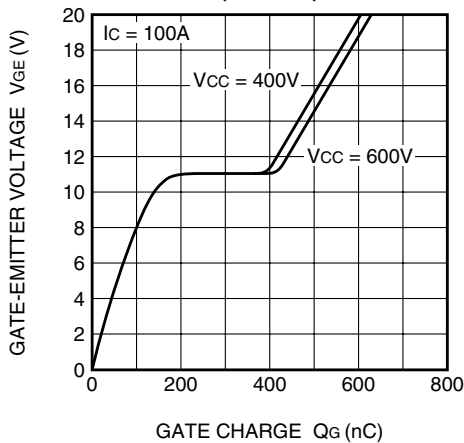
TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi part)



GATE CHARGE
CHARACTERISTICS
(TYPICAL)



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